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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HA17339/A Series

Quadruple Comparators



ADE-204-065A (Z)

Rev. 1

Mar. 2001

Description

The HA17339A and HA17339 series products are comparators designed for general purpose, especially for power control systems.

These ICs operate from a single power-supply voltage over a wide range of voltages, and feature a reduced power-supply current since the supply current is independent of the supply voltage.

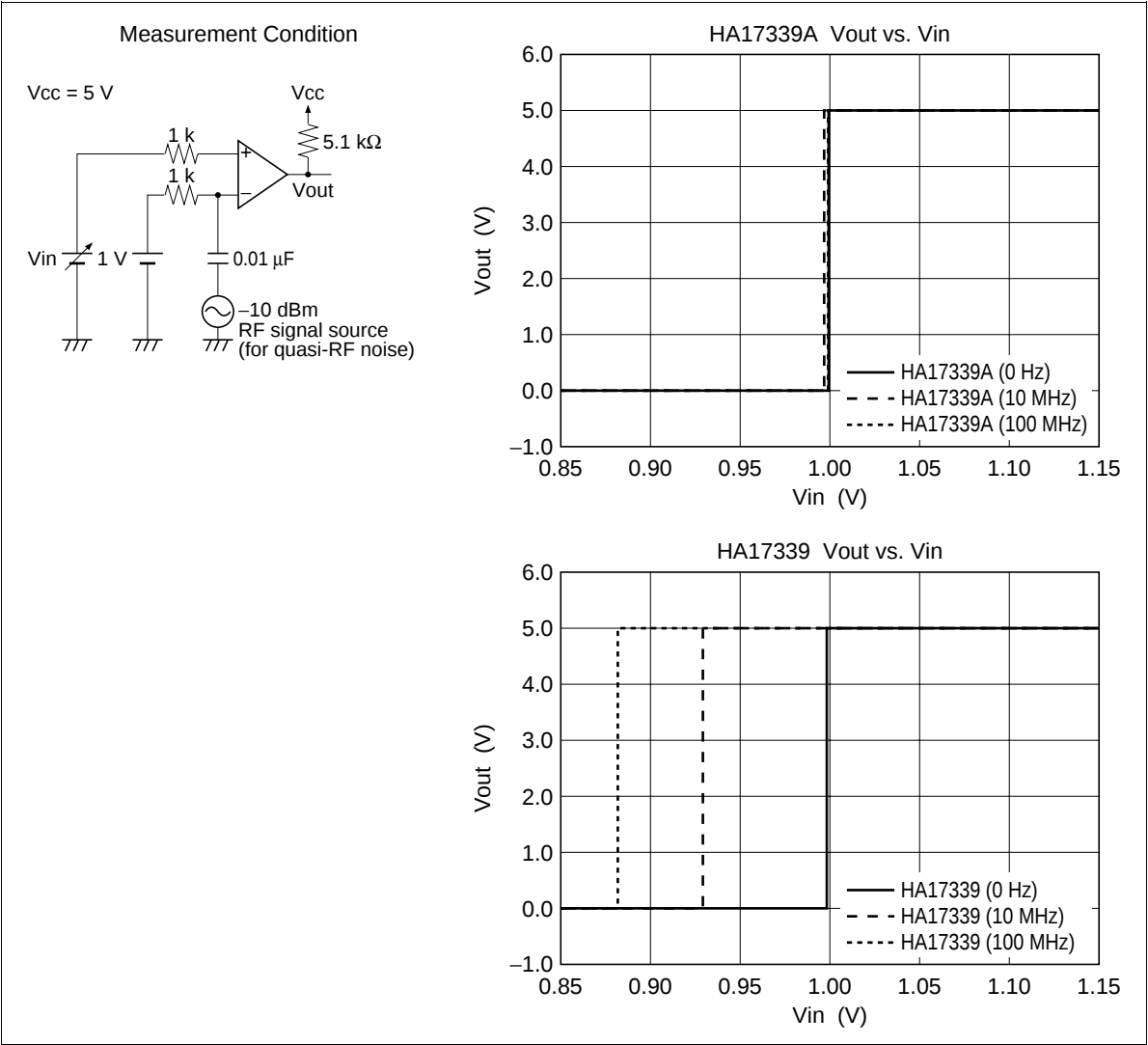
These comparators have the merit which ground is included in the common-mode input voltage range at a single-voltage power supply operation. These products have a wide range of applications, including limit comparators, simple A/D converters, pulse/square-wave/time delay generators, wide range VCO circuits, MOS clock timers, multivibrators, and high-voltage logic gates.

Features

- Wide power-supply voltage range: 2 to 36 V
- Very low supply current: 0.8 mA
- Low input bias current: 25 nA
- Low input offset current: 5 nA
- Low input offset voltage: 2 mV
- The common-mode input voltage range includes ground.
- Low output saturation voltage: 1 mV (5 μ A), 70 mV (1 mA)
- Output voltages compatible with CMOS logic systems

Features only for “A” series

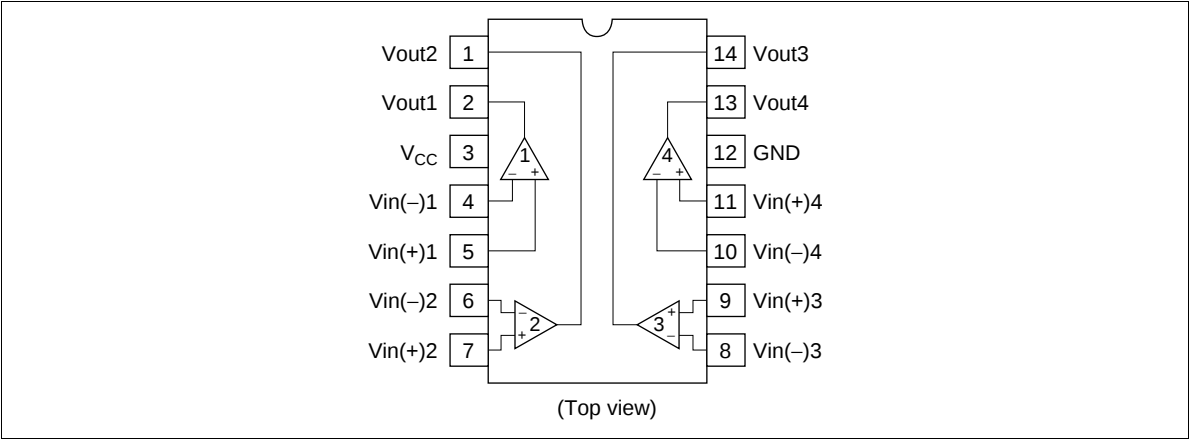
- Low electro-magnetic susceptibility



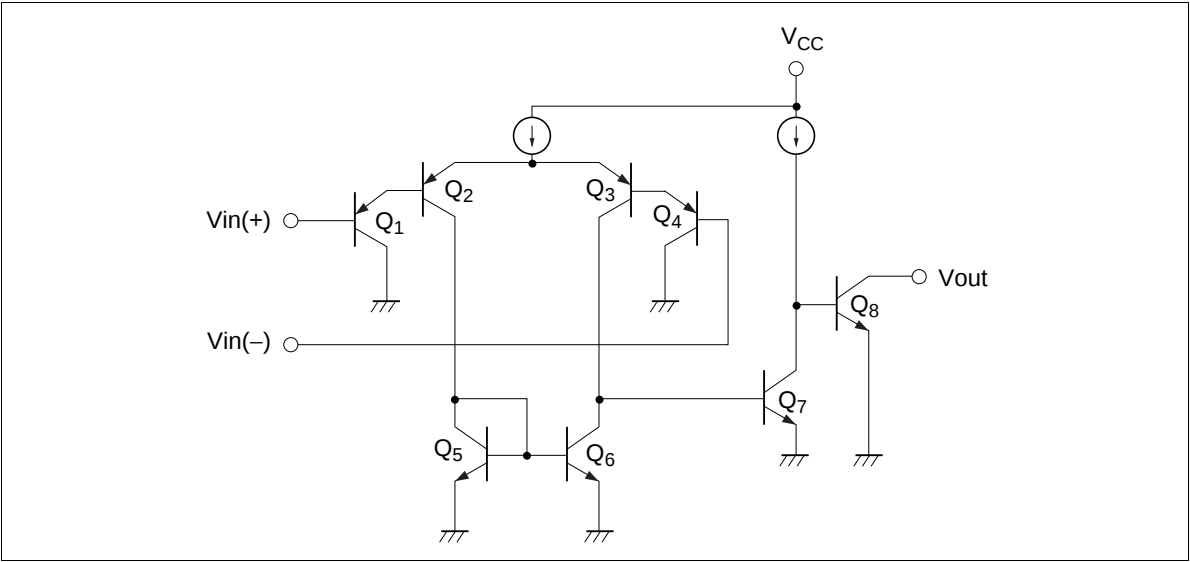
Ordering Information

Type No.	Application	Package
HA17339AP	Industrial use	DP-14
HA17339ARP	Commercial use	FP-14DN
HA17339AFP		FP-14DA
HA17339	Commercial use	DP-14
HA17339F		FP-14DA

Pin Arrangement



Circuit Structure (1/4)



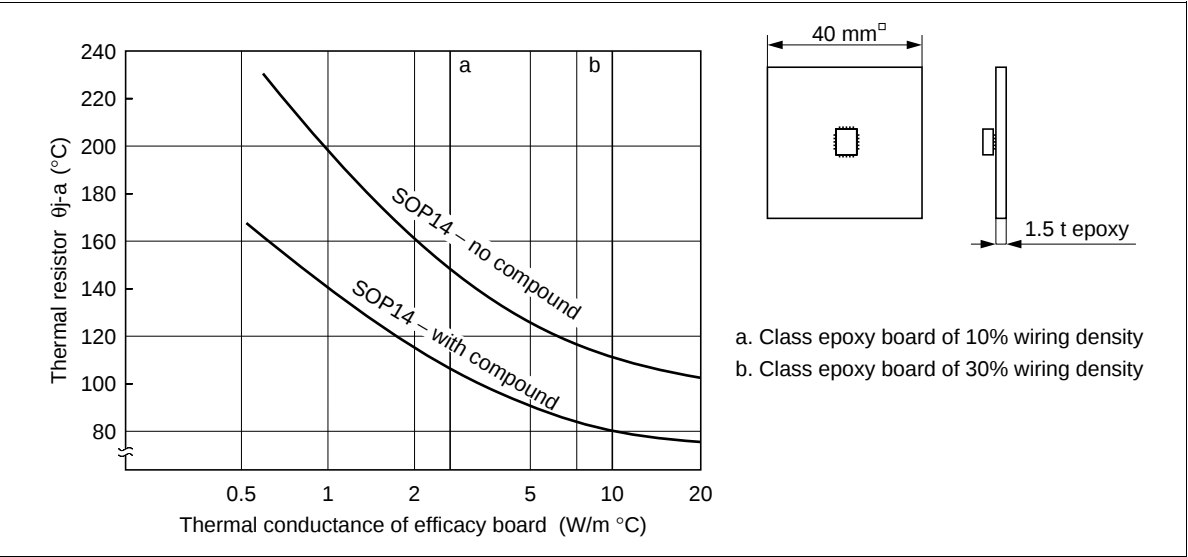
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings					Unit
		17339AP	17339AFP	17339ARP	17339	17339F	
Power supply voltage	V _{CC}	36	36	36	36	36	V
Differential input voltage	V _{in} (diff)	±V _{CC}	±V _{CC}	±V _{CC}	±V _{CC}	±V _{CC}	V
Input voltage	V _{in}	−0.3 to +V _{CC}	−0.3 to +V _{CC}	−0.3 to +V _{CC}	−0.3 to +V _{CC}	−0.3 to +V _{CC}	V
Output current	I _{out} *2	20	20	20	20	20	mA
Allowable power dissipation	P _T	625 *1	625 *3	625 *3	625 *1	625 *3	mW
Operating temperature	T _{opr}	−40 to +85	−40 to +85	−40 to +85	−20 to +75	−20 to +75	°C
Storage temperature	T _{stg}	−55 to +125	−55 to +125	−55 to +125	−55 to +125	−55 to +125	°C
Output pin voltage	V _{out}	36	36	36	36	36	V

- Notes: 1. These are the allowable values up to Ta = 50°C. Derate by 8.3 mW/°C above that temperature.
2. These products can be destroyed if the output and V_{CC} are shorted together. The maximum output current is the allowable value for continuous operation.
3. Tjmax = θj-a · P_Cmax + Ta (θj-a; Thermal resistor between junction and ambient at set board use).

The wiring density and the material of the set board must be chosen for thermal conductance of efficacy board.

And P_Cmax cannot be over the value of P_T.



Electrical Characteristics ($V_{CC} = 5\text{ V}$, $T_a = 25^\circ\text{C}$)

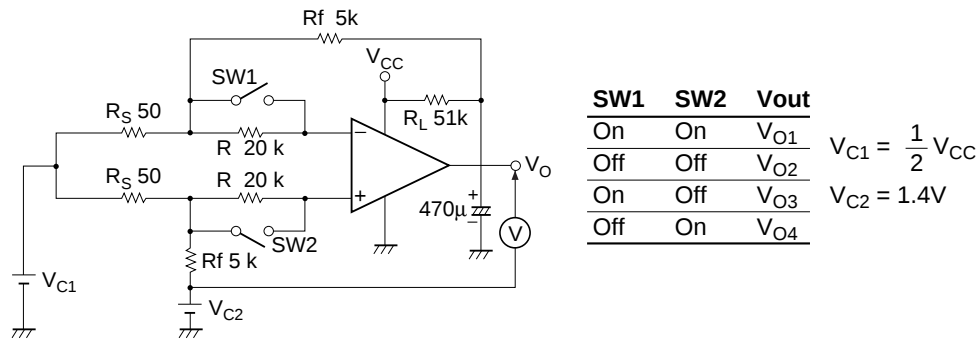
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Input offset voltage	V_{IO}	—	2	7	mV	Output switching point: when $V_O = 1.4\text{V}$, $R_S = 0\Omega$
Input bias current	I_{IB}	—	25	250	nA	$I_{IN(+)}$ or $I_{IN(-)}$
Input offset current	I_{IO}	—	5	50	nA	$I_{IN(+)} - I_{IN(-)}$
Common-mode input voltage * ¹	V_{CM}	0	—	$V_{CC} - 1.5$	V	
Supply current	I_{CC}	—	0.8	2	mA	$R_L = \infty$
Voltage Gain	A_V	—	200	—	V/mV	$R_L = 15\text{k}\Omega$
Response time * ²	t_R	—	1.3	—	μs	$V_{RL} = 5\text{V}$, $R_L = 5.1\text{k}\Omega$
Output sink current	I_{OSINK}	6	16	—	mA	$V_{IN(-)} = 1\text{V}$, $V_{IN(+)} = 0$, $V_O \leq 1.5\text{V}$
Output saturation voltage	$V_{O\text{ sat}}$	—	200	400	mV	$V_{IN(-)} = 1\text{V}$, $V_{IN(+)} = 0$, $I_{OSINK} = 3\text{mA}$
Output leakage current	I_{LO}	—	0.1	—	nA	$V_{IN(+)} = 1\text{V}$, $V_{IN(-)} = 0$, $V_O = 5\text{V}$

Notes: 1. Voltages more negative than -0.3 V are not allowed for the common-mode input voltage or for either one of the input signal voltages.

2. The stipulated response time is the value for a 100 mV input step voltage that has a 5 mV overdrive.

Test Circuits

1. Input offset voltage (V_{IO}), input offset current (I_{IO}), and Input bias current (I_{IB}) test circuit

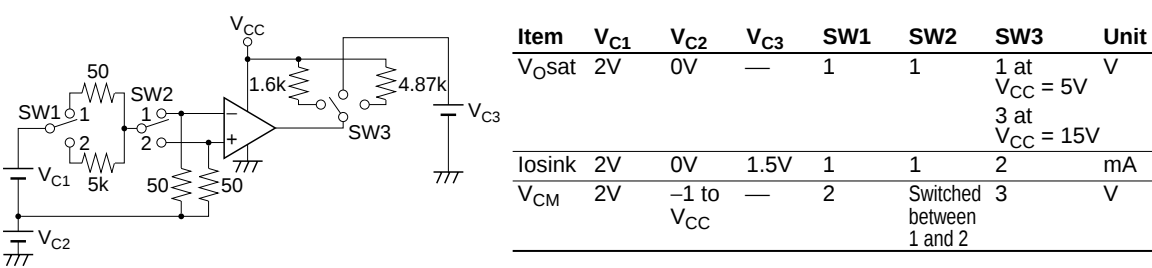


$$V_{IO} = \frac{|V_{O1}|}{1 + R_f / R_S} \quad (\text{mV})$$

$$I_{IO} = \frac{|V_{O2} - V_{O1}|}{R(1 + R_f / R_S)} \quad (\text{nA})$$

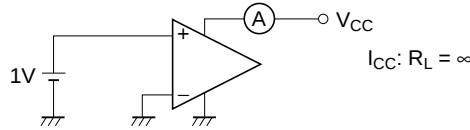
$$I_{IB} = \frac{|V_{O4} - V_{O3}|}{2 \cdot R(1 + R_f / R_S)} \quad (\text{nA})$$

2. Output saturation voltage ($V_O \text{ sat}$) output sink current (I_{osink}), and common-mode input voltage (V_{CM}) test circuit

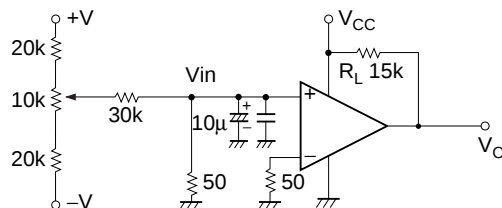


Item	V_{C1}	V_{C2}	V_{C3}	SW1	SW2	SW3	Unit
$V_{O\text{Sat}}$	2V	0V	—	1	1	1 at $V_{CC} = 5V$ 3 at $V_{CC} = 15V$	V
I_{osink}	2V	0V	1.5V	1	1	2	mA
V_{CM}	2V	-1 to V_{CC}	—	2	Switched between 1 and 2	3	V

3. Supply current (I_{CC}) test circuit

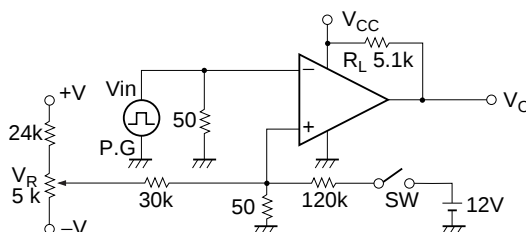


4. Voltage gain (A_V) test circuit ($R_L = 15k\Omega$)



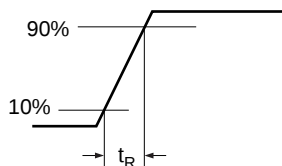
$$A_V = 20 \log \frac{V_{O1} - V_{O2}}{V_{IN1} - V_{IN2}} \quad (\text{dB})$$

5. Response time (t_R) test circuit



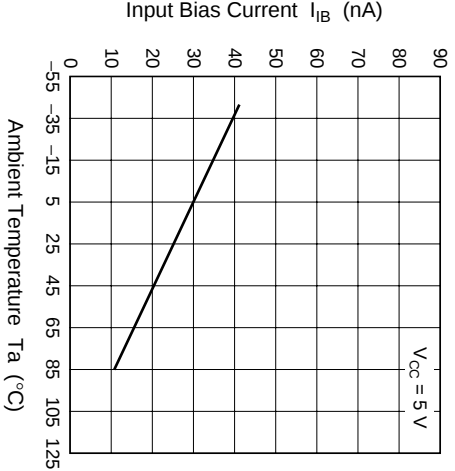
t_R : $R_L = 5.1k\Omega$, a 100mV input step voltage that has a 5mV overdrive

- With V_{IN} not applied, set the switch SW to the off position and adjust V_R so that V_O is in the vicinity of 1.4V.
- Apply V_{IN} and turn the switch SW on.

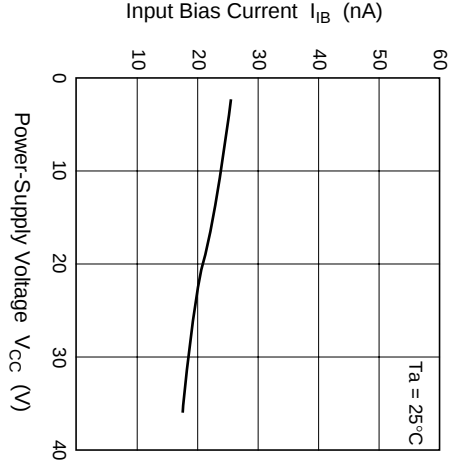


Characteristic Curves

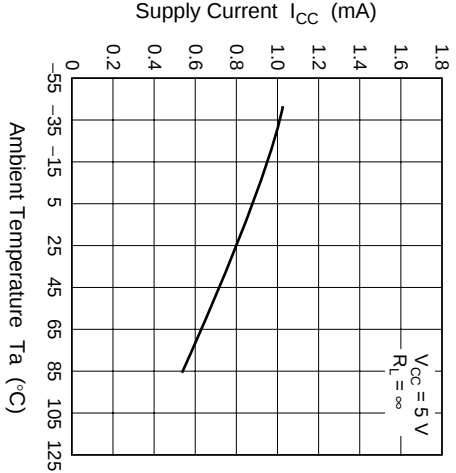
Input Bias Current vs.
Ambient Temperature Characteristics



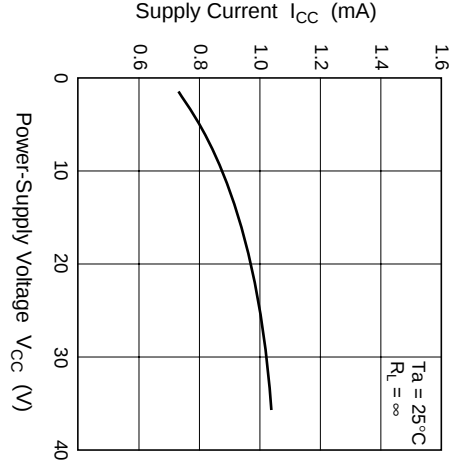
Input Bias Current vs.
Power-Supply Voltage Characteristics



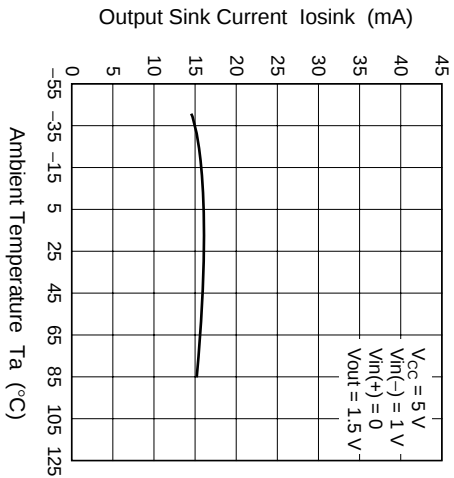
Supply Current vs.
Ambient Temperature Characteristics



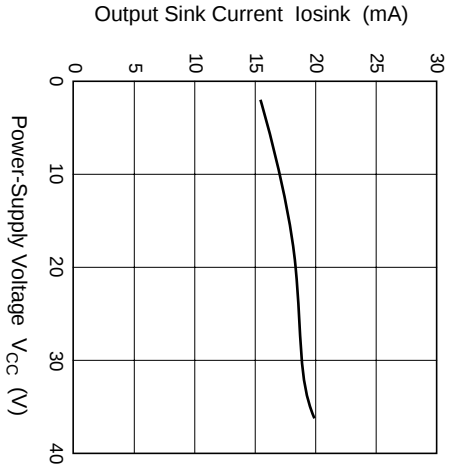
Supply Current vs.
Power-Supply Voltage Characteristics



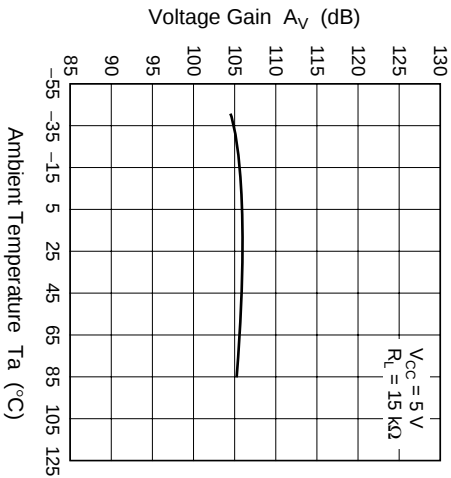
Output Sink Current vs.
Ambient Temperature Characteristics



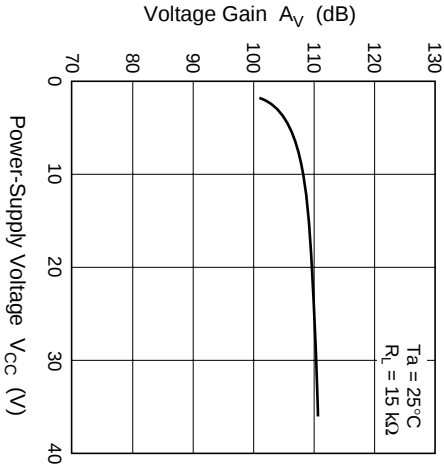
Output Sink Current vs.
Power-Supply Voltage Characteristics



Voltage Gain vs.
Ambient Temperature Characteristics



Voltage Gain vs.
Power-Supply Voltage Characteristics



HA17339/A Application Examples

The HA17339/A houses four independent comparators in a single package, and operates over a wide voltage range at low power from a single-voltage power supply. Since the common-mode input voltage range starts at the ground potential, the HA17339/A is particularly suited for single-voltage power supply applications. This section presents several sample HA17339/A applications.

HA17339/A Application Notes

1. Square-Wave Oscillator

The circuit shown in figure one has the same structure as a single-voltage power supply astable multivibrator. Figure 2 shows the waveforms generated by this circuit.

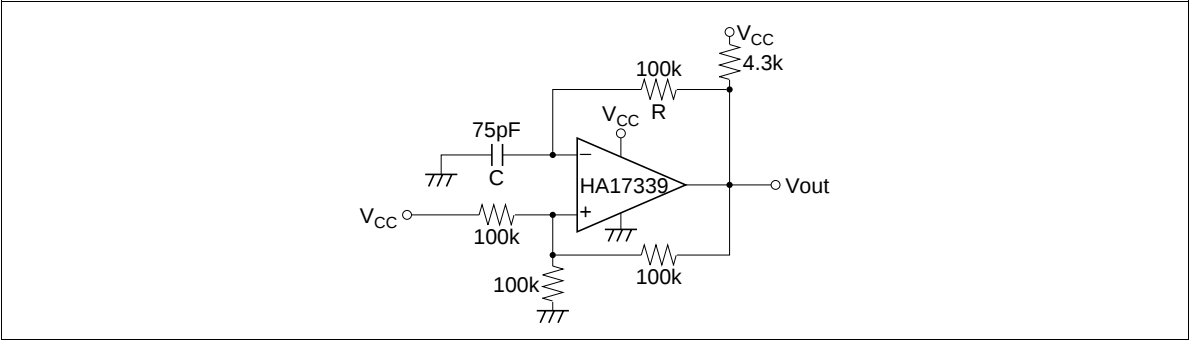


Figure 1 Square-Wave Oscillator

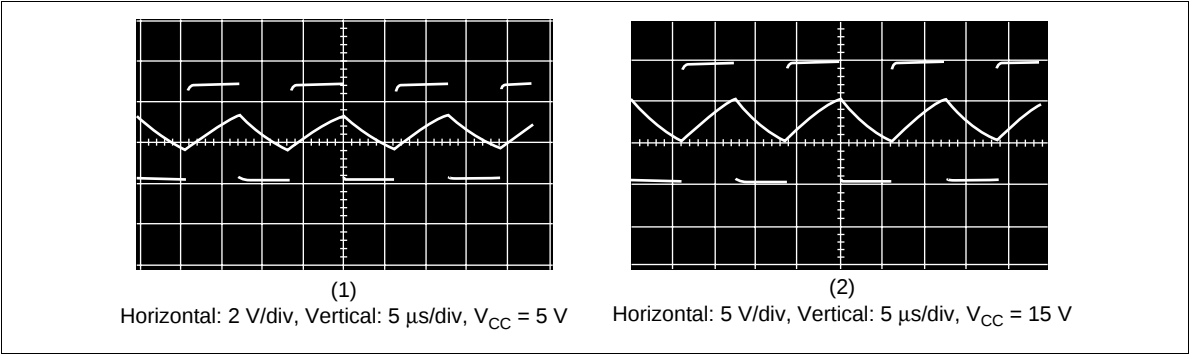


Figure 2 Operating Waveforms

2. Pulse Generator

The charge and discharge circuits in the circuit from figure 1 are separated by diodes in this circuit. (See figure 3.) This allows the pulse width and the duty cycle to be set independently. Figure 4 shows the waveforms generated by this circuit.

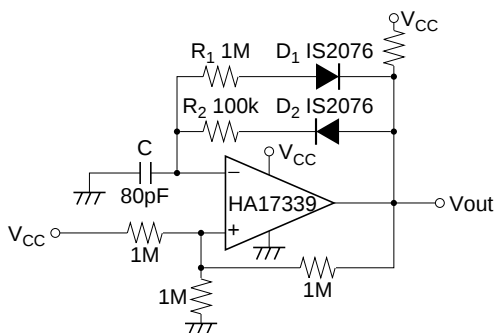
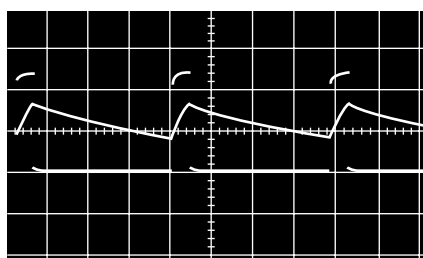
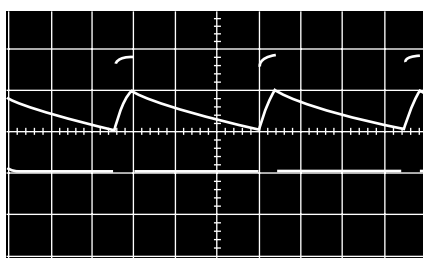


Figure 3 Pulse Generator



Horizontal: 2 V/div, Vertical: 20 μ s/div, $V_{CC} = 5$ V



Horizontal: 5 V/div, Vertical: 20 μ s/div, $V_{CC} = 15$ V

Figure 4 Operating Waveforms

3. Voltage Controlled Oscillator

In the circuit in figure 5, comparator A_1 operates as an integrator, A_2 operates as a comparator with hysteresis, and A_3 operates as the switch that controls the oscillator frequency. If the output V_{out1} is at the low level, the A_3 output will go to the low level and the A_1 inverting input will become a lower level than the A_1 noninverting input. The A_1 output will integrate this state and its output will increase towards the high level. When the output of the integrator A_1 exceeds the level on the comparator A_2 inverting input, A_2 inverts to the high level and both the output V_{out1} and the A_3 output go to the high level. This causes the integrator to integrate a negative state, resulting in its output decreasing towards the low level. Then, when the A_1 output level becomes lower than the level on the A_2 noninverting input, the output V_{out1} is once again inverted to the low level. This operation generates a square wave on V_{out1} and a triangular wave on V_{out2} .

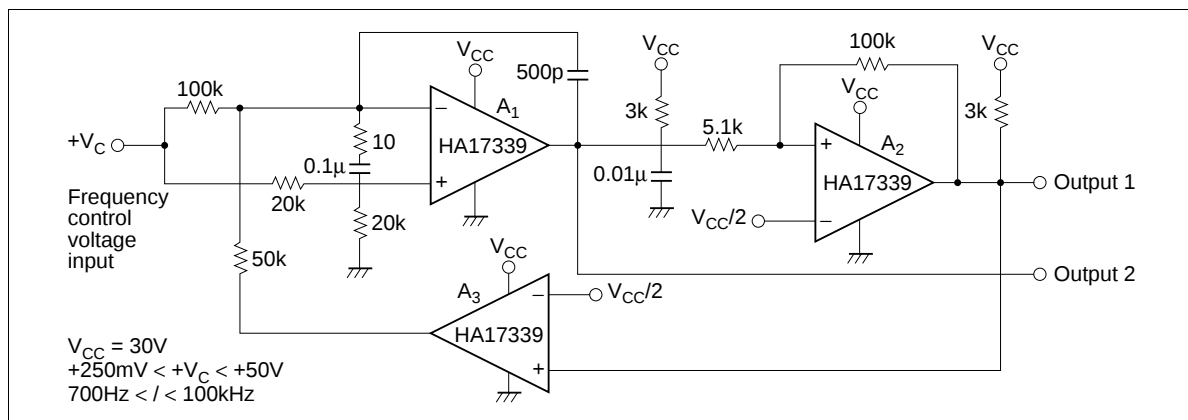


Figure 5 Voltage Controlled Oscillator

4. Basic Comparator

The circuit shown in figure 6 is a basic comparator. When the input voltage V_{IN} exceeds the reference voltage V_{REF} , the output goes to the high level.

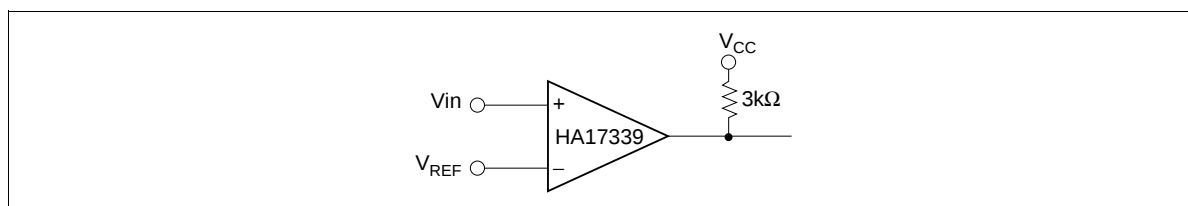


Figure 6 Basic Comparator

5. Noninverting Comparator (with Hysteresis)

Assuming $+V_{IN}$ is 0V, when V_{REF} is applied to the inverting input, the output will go to the low level (approximately 0V). If the voltage applied to $+V_{IN}$ is gradually increased, the output will go high when the value of the noninverting input, $+V_{IN} \times R_2 / (R_1 + R_2)$, exceeds $+V_{REF}$. Next, if $+V_{IN}$ is gradually lowered, V_{out} will be inverted to the low level once again when the value of the noninverting input, $(V_{out} - V_{IN}) \times R_1 / (R_1 + R_2)$, becomes lower than V_{REF} . With the circuit constants shown in figure 7, assuming $V_{CC} = 15V$ and $+V_{REF} = 6V$, the following formula can be derived, i.e. $+V_{IN} \times 10M / (5.1M + 10M) > 6V$, and V_{out} will invert from low to high when $+V_{IN}$ is $> 9.06V$.

$$(V_{out} - V_{IN}) \times \frac{R_1}{R_1 + R_2} + V_{IN} < 6V$$

(Assuming $V_{out} = 15V$)

When $+V_{IN}$ is lowered, the output will invert from high to low when $+V_{IN} < 1.41V$. Therefore this circuit has a hysteresis of 7.65V. Figure 8 shows the input characteristics.

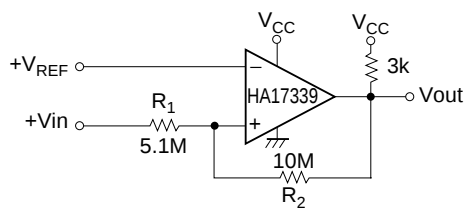


Figure 7 Noninverting Comparator

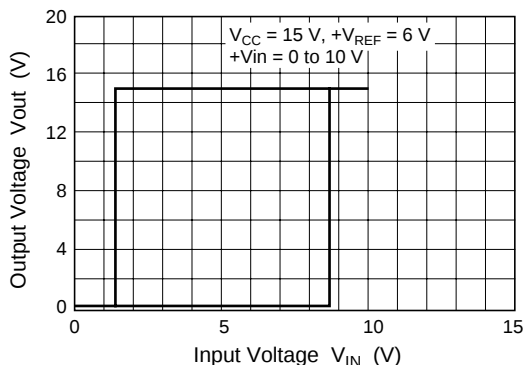


Figure 8 Noninverting Comparator I/O Transfer Characteristics

6. Inverting Comparator (with Hysteresis)

In this circuit, the output V_{out} inverts from high to low when $+V_{IN} > (V_{CC} + V_{out})/3$. Similarly, the output V_{out} inverts from low to high when $+V_{IN} < V_{CC}/3$. With the circuit constants shown in figure 9, assuming $V_{CC} = 15V$ and $V_{out} = 15V$, this circuit will have a 5V hysteresis. Figure 10 shows the I/O characteristics for the circuit in figure 9.

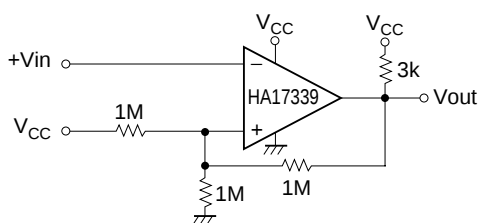


Figure 9 Inverting Comparator

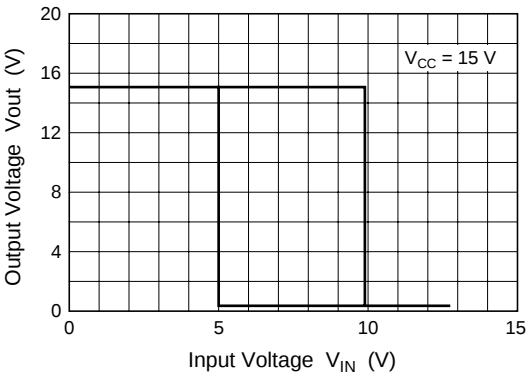


Figure 10 Inverting Comparator I/O Transfer Characteristics

7. Zero-Cross Detector (Single-Voltage Power Supply)

In this circuit, the noninverting input will essentially be held at the potential determined by dividing V_{CC} with $100k\Omega$ and $10k\Omega$ resistors. When V_{IN} is 0V or higher, the output will be low, and when V_{IN} is negative, V_{out} will invert to the high level. (See figure 11.)

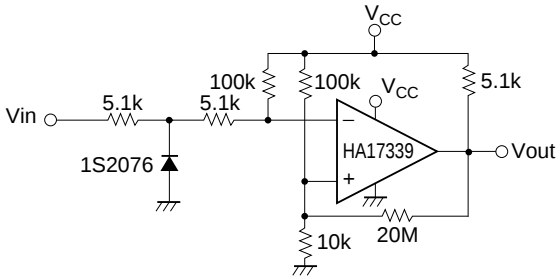
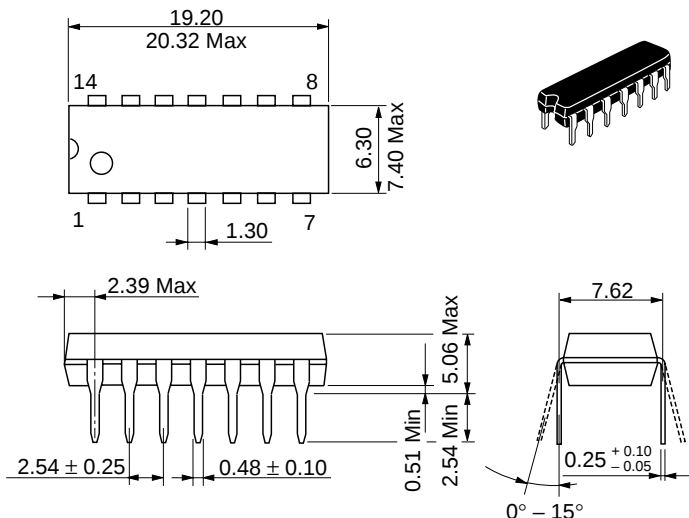


Figure 11 Zero-Cross Detector

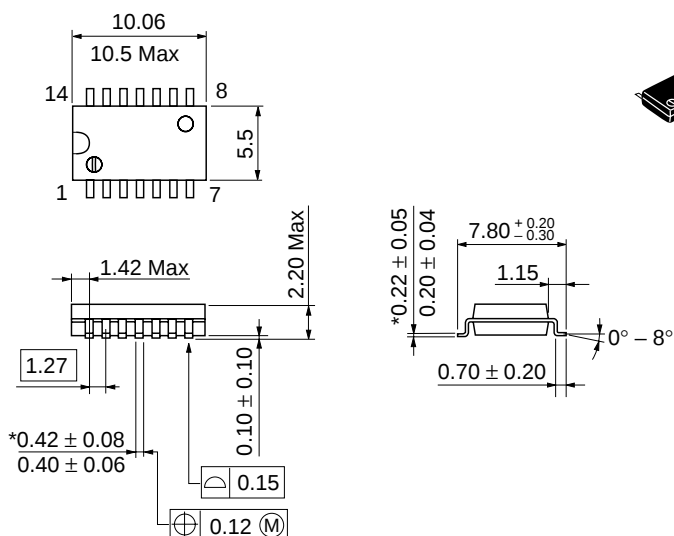
Package Dimensions

Unit: mm



Hitachi Code	DP-14
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.97 g

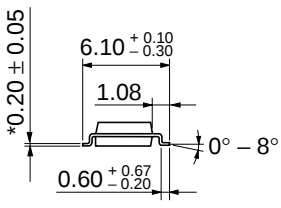
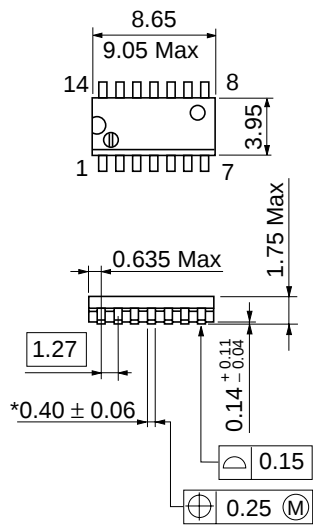
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-14DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.23 g

Unit: mm



*Pd plating

Hitachi Code	FP-14DN
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.13 g

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